

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Application Number	Unknown	
				Filing Date	Unknown	
				First Named Inventor:	WOHLMUTH, Walter A.	
				Examiner name: Unknown	GROUP: Unknown	
Sheet	1	of	1	Attorney Docket Number	TRQ-00004	
U.S. PUBLISHED PATENT APPLICATIONS						
Examiner Initials*	Cited No. ¹	<u>U.S. Patent Document</u> Number Kind Code ² <i>(if known)</i>		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines Where Relevant Info. Appear
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	Ko, Dae-Hong and Robert Sinclair, "In-situ dynamic high-resolution transmission electron microscopy: application to Pt/GaAs interfacial reactions," Ultramicroscopy, 54, pp. 166-178 (1994)					
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.